# MMBD217SEW

## SILICON EPITAXIAL PLANAR SWITCHING DIODE

#### Applications

Ultra high speed switching





SOT-323 Plastic Package Marking Code: **A7** 

### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V <sub>RM</sub>	80	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Rectified Forward Current (Single)	Ι <sub>ο</sub>	100	mA
Maximum (Peak) Forward Current (Single)	I <sub>FM</sub>	300	mA
Peak Forward Surge Current ( $t_p = 1 \ \mu s$ )	I <sub>FSM</sub>	4	А
Power Dissipation	P <sub>d</sub>	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>s</sub>	- 55 to + 150	°C

#### Characteristics at T<sub>a</sub> = 25 °C

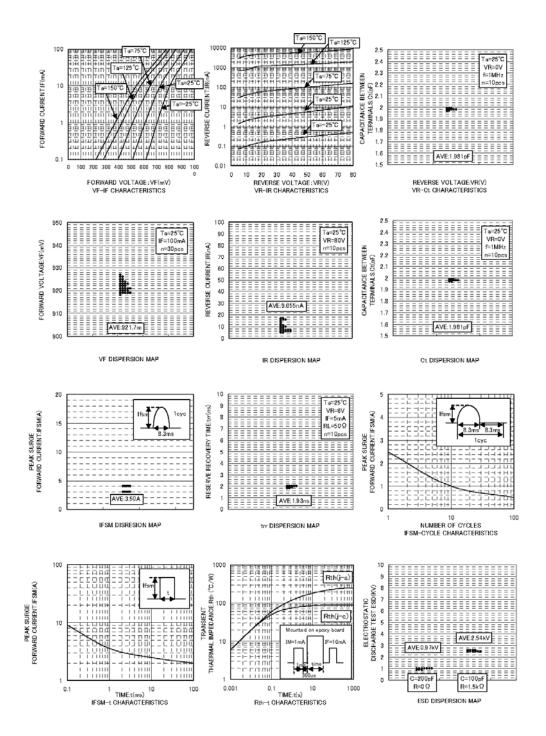
Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	V <sub>F</sub>	1.2	V
Reverse Current at $V_R$ = 70 V	I <sub>R</sub>	0.1	μΑ
Capacitance between Terminals at $V_R$ = 6, f = 1 MHz	CT	3.5	pF
Reverse Recovery Time at $I_F$ = 5 mA, $V_R$ = 6 V, $R_L$ = 50 $\Omega$	t <sub>rr</sub>	4	ns







Dated : 10/10/2008





SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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